

## **Supporting Information**

### **Dipole Tuning of Charge Transport in Molecular Junctions**

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Highly doped ( $p^+$ ) Si surfaces were modified with molecules belonging to ethynylbenzene series. The molecules are attached covalently to the silicon surface by thermo-chemical reaction. X-ray photoelectron spectroscopic measurements are done for the modified surfaces using ESCALAB spectrometer at a take-off angle  $35^\circ$  and pressure of  $10^{-11}$  torr. The spectra for  $p^+$ -Si surfaces modified with EBZ and DEBZ molecules are shown below. It showed Si (2p) peak at 99.8 eV and C-peak around 285 eV indicating molecular bonding to Si surface. There was no presence of oxygen or any other contamination.

